

APPLICATION BRIEF

Introduction to HF Vapor Etch

Introduction

Nearly all silicon MEMS devices are created using a sacrificial silicon oxide layer, which when removed, “releases” the silicon MEMS structure and allows free movement.

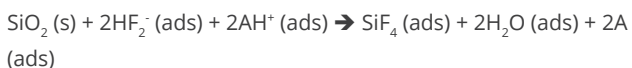
Silicon oxide is typically etched by hydrogen fluoride :



The most widespread method of HF based etch release is wet chemical etching using a mixture of HF and water. However, as the HF, or subsequent rinsing solutions, dry it can cause “stiction”, by pulling the free-moving microstructures together which remain adhered to each other after release, reducing device yields. Another potential issue with wet HF etching is that it will corrode any exposed metals, most notably aluminium, on the wafer.

To avoid these issues, dry HF vapor can be used. A gaseous etchant also penetrates smaller features more easily and allows longer undercuts.

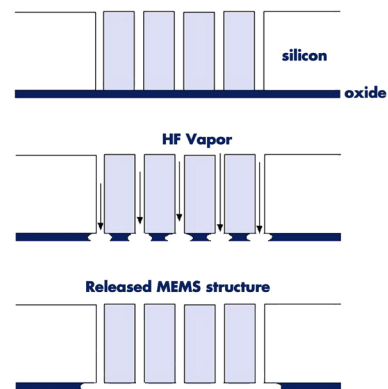
Alcohol (A) ionises the HF vapor and acts as a catalyst:



Water, a by-product of the reaction, also acts as a catalyst and must therefore be carefully controlled and removed from the system.

SPTS’s patented Primaxx HF/Alcohol process employs a reduced pressure, gas phase environment for the isotropic etch removal of sacrificial oxide layers.

The process is generally carried out at pressures between 75 and 150 torr providing controlled, residue-free etching. Typical vertical and lateral oxide etch rates are in the 0.1 - 10 microns/minute range.



Schematic illustration of HF vapor release etch

Why Use Dry Release Etch?

- Eliminates stiction with device yields typically ~ 100%
- Provides repeatable, stable performance with a wide process window
- Compatible with a wide range of metals, especially unprotected Al mirrors and bond pads
- No complex waste management issues, small footprint, no process consumables
- Low cost of ownership

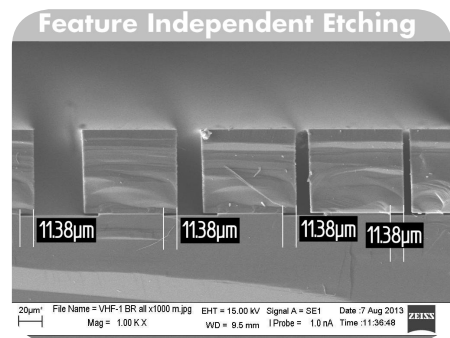
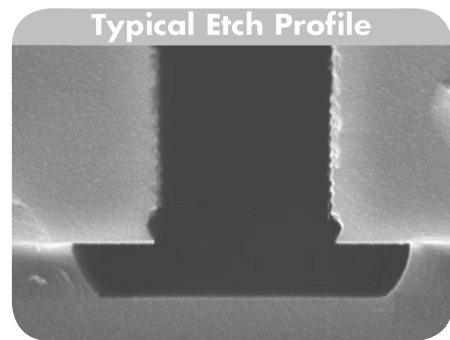
Why Use Reduced Pressure?

- Keeps etch by-products in the gas phase ensuring high selectivities to metals
- Maximum feature penetration without localized loading effects
- Broad process window for optimizing productivity and etch results

Material Compatibility

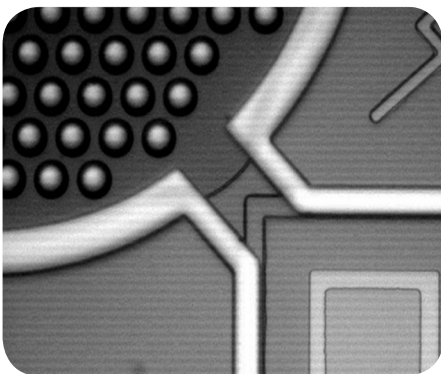
Material	Sacrificial Oxide	Protective Layer	Metal/ Electrode / Adhesion
Thermal oxide, TEOS	●		
SOI bonded oxide	●		
Quartz	●		
PECVD oxide	●		
Spin on oxide	●		
Alumina		●	
ALD alumina		●	
Aluminium		●	●
Silicon carbide		●	
Si-rich LPCVD nitride		●	
Gold			●
Copper			●
TiW			●
Nickel			●

Isotropic Etching

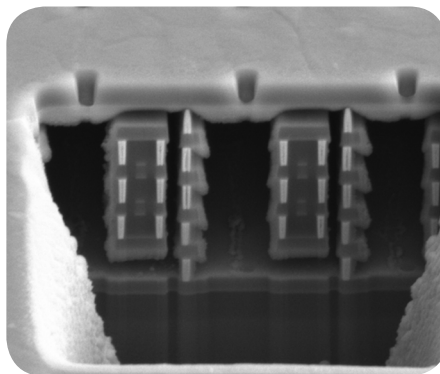


Images courtesy of
RAFAEL – Advanced Defense Systems LTD

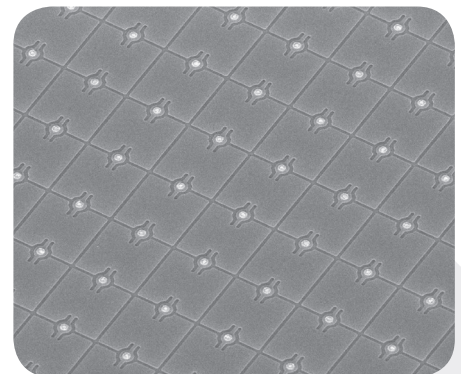
Application Examples



MEMS microphone



CMOS MEMS
(Image courtesy of Baolab Microsystems)



MEMS micromirror array
(Image courtesy of FhG-IPMS)

Product Range

SPTS offers a choice of HF vapor etch systems for R&D to volume production applications:

- **Primaxx® Monarch300** - a 13-wafer batch process modules for 200mm or 300mm wafers, for high volume production applications in either the Primaxx® fxP or Primaxx® c2L configurations.
- **Primaxx® Monarch25** - a 25-wafer batch process module for wafer up to 200mm, in volume production, compatible with the Primaxx® fxP or Primaxx® c2L
- **Primaxx® Monarch3** - compact module includes a three-wafer process chamber, and is designed for research laboratory and small volume production environments.
- **Primaxx® uEtch** - single-wafer system specifically designed for university and small research laboratories.

uEtch



Monarch300



SPTS Technologies, A KLA company, designs, manufactures, sells, and supports etch, PVD, CVD and MVD® wafer processing solutions for the MEMS, advanced packaging, LED, high speed RF on GaAs, and power management device markets. For more information about SPTS Technologies, email enquiries@spts.com or visit www.spts.com